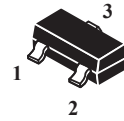


Surface Mount Switching Diode

Features:

- *Low Current Leakage
- *Low Forward Voltage
- *Reverse Recover Time $T_{rr} \leq 4ns$
- *Small Outline Surface Mount SOT-23 Package

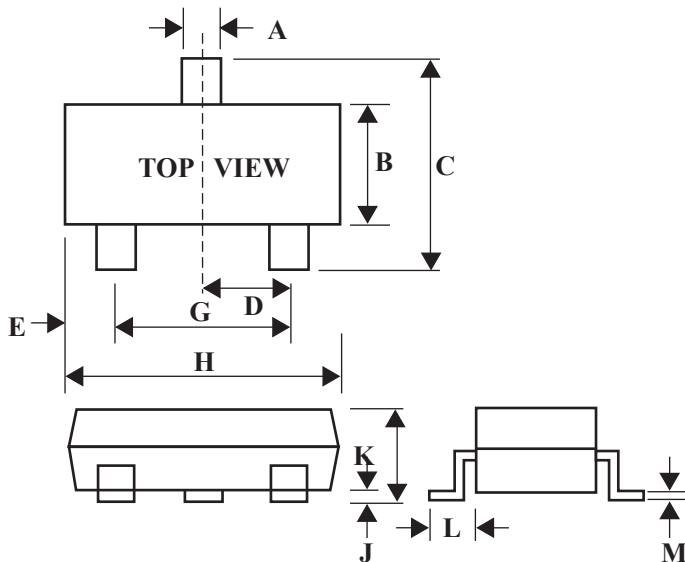
SWITCHING DIODE
100-200m AMPERRES
75-100 VOLTS



SOT-23

SOT-23 Outline Dimensions

Unit:mm



Dim	Min	Max
A	0.35	0.51
B	1.19	1.40
C	2.10	3.00
D	0.85	1.05
E	0.46	1.00
G	1.70	2.10
H	2.70	3.10
J	0.01	0.13
K	0.89	1.10
L	0.30	0.61
M	0.076	0.25

Maximum Ratings (EACH DIODE)

Characteristic	Symbol	MMBD2836	MMBD2838	MMBD7000	Unit
Reverse Voltage	V _R	75		100	Volts
Forward Current	I _F	100		200	mAdc
Peak Forward Surge Current	I _{FM}	500			mAdc

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board *1, TA=25°C Derate Above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	556	°C/W
Total Device Dissipation Alumina Substrate*2 TA=25°C Derate Above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	417	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to + 150	°C

*1 ER-5=1.0x0.75x0.062 in

*2 Alumina=0.4x0.3x0.024 in 99.5% Alumina

Electrical Characteristics (TA=25°C Unless Otherwise Note) (Each Diode)

Characteristic	Symbol	Min	Max	Unit
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Off Characteristics

Reverse Breakdown Voltage(I _{BR} =100μAdc) MMBD2836/MMBD2838 MMBD7000	V _{BR}	75 100	-	Vdc
Reverse Voltage Leakage Current V _R =50V MMBD2836/MMBD2838 MMBD7000	I _R	-	0.1 1.0	μAdc
V _R =100V MMBD7000			3.0	
V _R =50V, T _J =125°C MMBD7000			100	

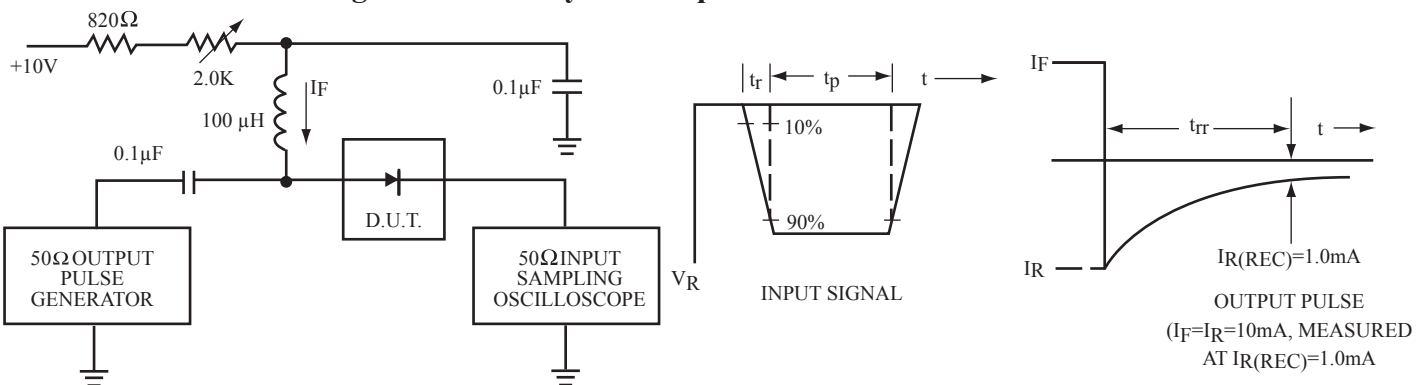
Off Characteristic

Characteristic	Symbol	Min	Max	Unit
Diode Capacitance MMBD2836/MMBD2838 ($V_R=0, f=1.0\text{MHz}$) MMBD7000	C_D		4.0 1.5	PF
Forward Voltage ($I_F=1.0\text{ mAdc}$) MMBD7000 ($I_F=10\text{ mAdc}$) MMBD2836/MMBD2838 MMBD7000 ($I_F=50\text{ mAdc}$) MMBD2836/MMBD2838 ($I_F=100\text{ mAdc}$) MMBD2836/MMBD2838 MMBD7000	V_F		700 1000 820 1000 1200 1100	mVdc
Reverse Recovery Time (Figure 1.) $I_F=I_R=10\text{ mAdc}, V_R=5.0\text{Vdc}$ $I_R(\text{REC})=1.0\text{ mAdc}, R_L=100$	t_{rr}		4.0	nS

Device Marking

Item	Marking	Equivalent Circuit diagram
MMBD2838	A6	
MMBD2836	A2	
MMBD7000	M5C	

Figure 1. Recovery Time Equivalent Test Circuit



- Notes: 1. A 2.0 kΩ variable resistor for a Forward Current (I_F) of 10 mA
 2. Input pulses is adjusted so $I_R(\text{peak})$ is equal to 10 mA
 3. $t_p \gg t_{rr}$

FIGURE 2. FORWARD VOLTAGE

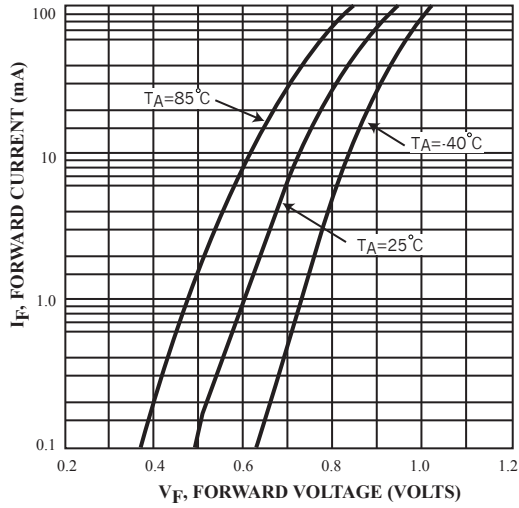


FIGURE 3. LEAKAGE CURRENT

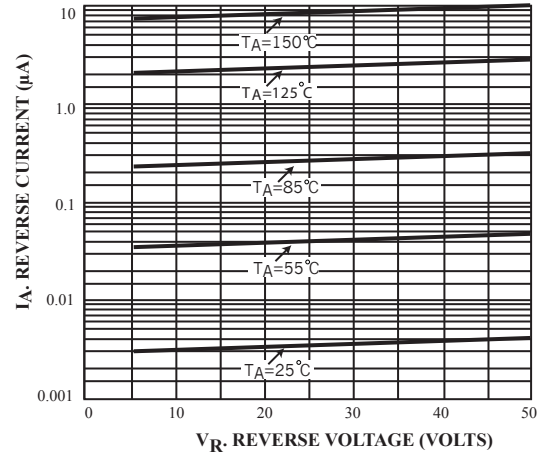


FIGURE 4. CAPACITANCE(2836)

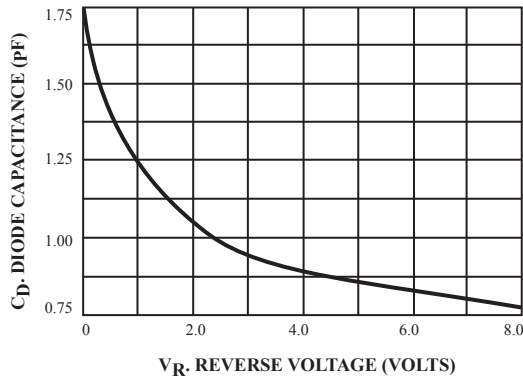


FIGURE 5. CAPACITANCE(2838)

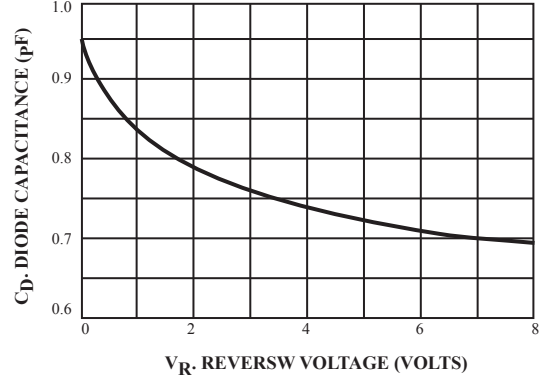


FIGURE 6. CAPACITANCE(7000)

